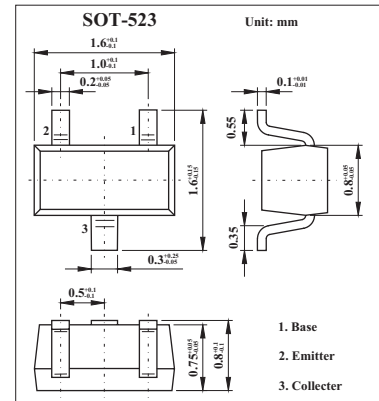


Silicon PNP Epitaxial Type Transistor 2SA1832

■ Features

- High Voltage and High Current : $V_{CE0} = -50V, I_C = -150mA$ (Max.)
- Excellent h_{FE} Linearity :
 $h_{FE}(I_C = -0.1mA) / h_{FE}(I_C = -2mA) = 0.95$ (Typ.)
- High h_{FE} : $h_{FE} = 70$ to 400



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CB0}	-50	V
Collector-emitter voltage	V_{CE0}	-50	V
Emitter-base voltage	V_{EB0}	-5	V
Collector current	I_C	-150	mA
Base current	I_B	-30	mA
Collector power dissipation	P_C	100	mW
Junction temperature	T_j	125	$^\circ C$
Storage temperature	T_{stg}	-55 to +125	$^\circ C$

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = -5V, I_E = 0$			-0.1	μA
Emitter cutoff current	I_{EBO}	$V_{EB} = -5V, I_C = 0$			-0.1	μA
DC current Gain	h_{FE}	$V_{CE} = -6V, I_C = -2mA$	70		400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -100mA, I_B = -10mA$		-0.1	-0.3	V
Collector Output Capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$		4	7	pF
Transition frequency	f_T	$V_{CE} = -10V, I_C = -1mA$	80			MHz

■ h_{FE} Classification

Marking	SQ	SY	SG
Rank	Q	Y	GR
h_{FE}	70~140	120~240	200~400